Supplementary Information

for

Electron-Interfered Field-Effect Transistors as Sensor Platform for Detecting a Delicate Surface Chemical Reaction

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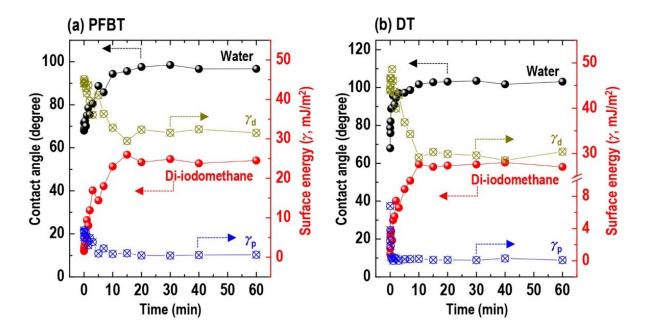


Figure S1. Variations in the contact angles using D.I. water and diiodomethane or the dispersive (γ_d) and polar (γ_p) surface energies of IE surface according to the reaction time. (a) PFBT and (b) DT cases.